

Silicon NPN Power Transistors

2SC4544

**DESCRIPTION**

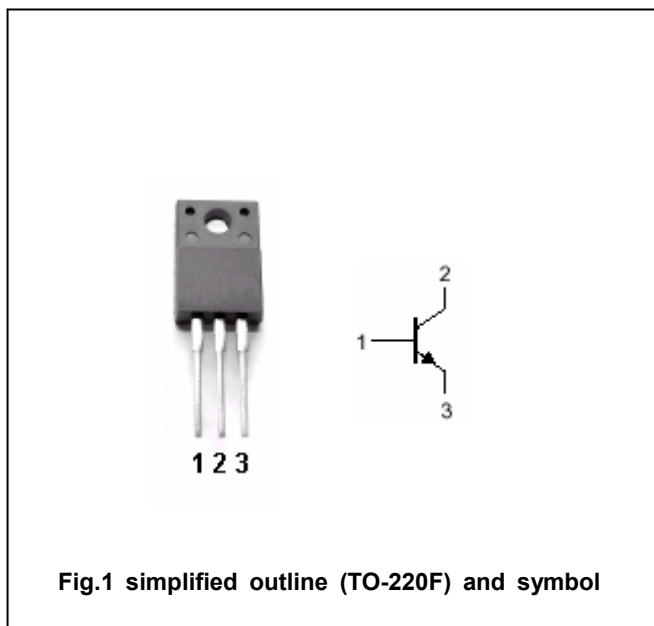
- With TO-220F package
- High Voltage

**APPLICATIONS**

- Color TV horizontal driver applications
- Color TV chroma output applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



**Absolute maximum ratings (Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	300	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	300	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7	V
I <sub>C</sub>	Collector current		100	mA
I <sub>B</sub>	Base current		50	mA
P <sub>C</sub>	Collector power dissipation	T <sub>a</sub> =25°C	2	W
		T <sub>C</sub> =25°C	8	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =100μA; I <sub>B</sub> =0	300			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =10μA; I <sub>C</sub> =0	7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =10mA ; I <sub>B</sub> =1m A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =10mA ; I <sub>B</sub> =1m A			1.0	V
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =4mA ; V <sub>CE</sub> =10V	20			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =20mA ; V <sub>CE</sub> =10V	30		200	
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =240V; I <sub>E</sub> =0			1.0	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =7V; I <sub>C</sub> =0			1.0	μA
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =20V; f=1MHz		3		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =20mA ; V <sub>CE</sub> =10V	50	70		MHz

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PACKAGE OUTLINE

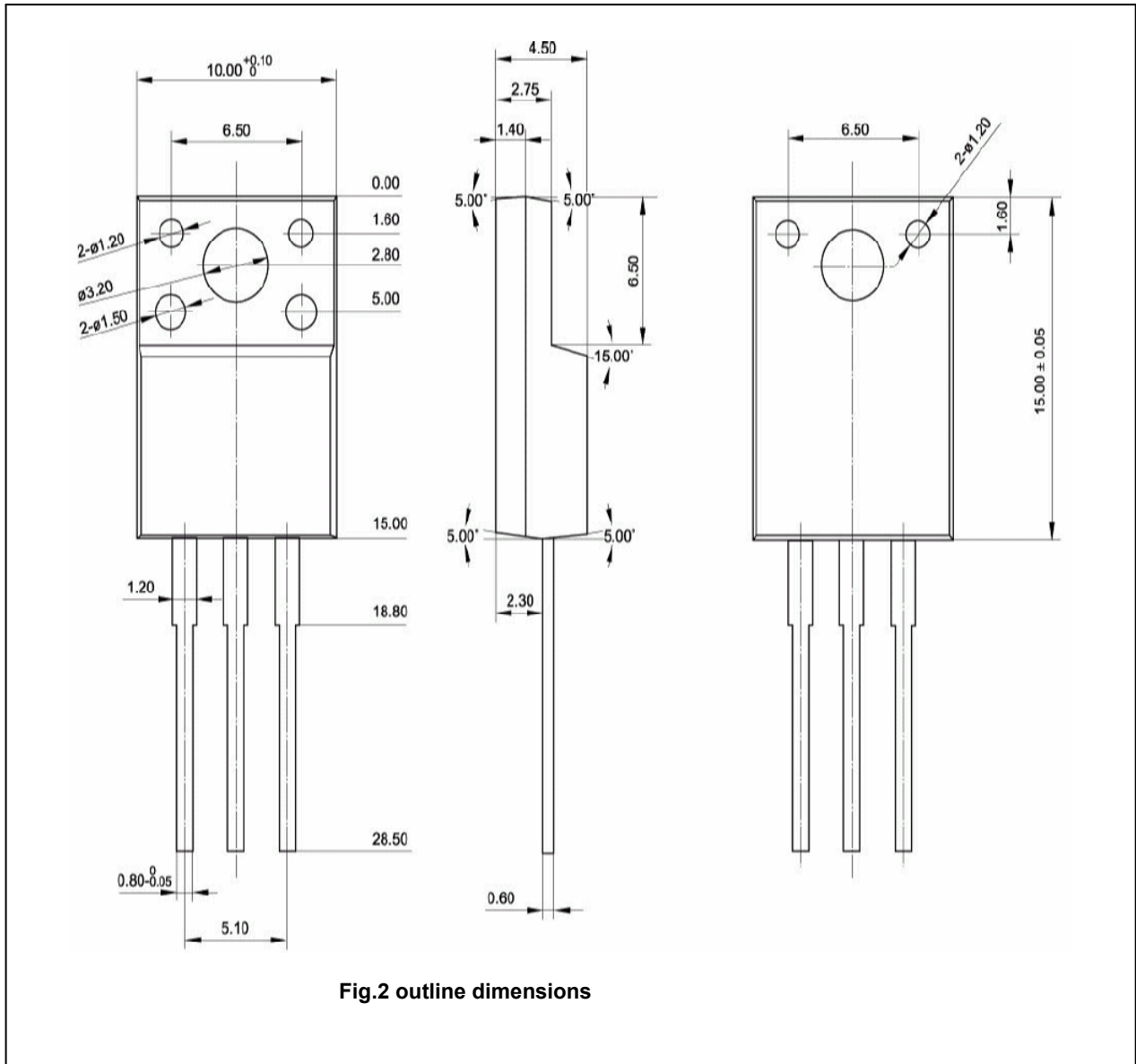


Fig.2 outline dimensions